

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	("6818948").PN.	USPAT	OR	OFF	2005/03/31 10:54
L2	1	("6093606").PN.	USPAT	OR	OFF	2005/03/31 10:54
L3	1	1 and (trench or long or parallel or tunnel or oxide or isolation or source or drain or polysilicon or control or gate or plurality or pair or floating or region or electrically or bottom or memory or cell or side or wall or spacer or silicon or nitride or pad or shallow or dielectric or insulating or cvd or cmp or etch or etching or RTA)	USPAT	OR	ON	2005/03/31 10:54
L4	1	2 and (trench or long or parallel or tunnel or oxide or isolation or source or drain or polysilicon or control or gate or plurality or pair or floating or region or electrically or bottom or memory or cell or side or wall or spacer or silicon or nitride or pad or shallow or dielectric or insulating or cvd or cmp or etch or etching or RTA)	USPAT	OR	ON	2005/03/31 10:54
L5	2460	438/257	USPAT	OR	ON	2005/03/31 10:55
L6	916	438/259	USPAT	OR	ON	2005/03/31 10:55
L7	551	438/263	USPAT	OR	ON	2005/03/31 10:55
L8	1310	438/264	USPAT	OR	ON	2005/03/31 10:55
L9	534	438/267	USPAT	OR	ON	2005/03/31 10:55
L10	965	438/270	USPAT	OR	ON	2005/03/31 10:56
L11	795	438/286	USPAT	OR	ON	2005/03/31 10:56
L12	836	438/289	USPAT	OR	ON	2005/03/31 10:56
L13	1121	438/680	USPAT	OR	ON	2005/03/31 10:56
L14	563	438/681	USPAT	OR	ON	2005/03/31 10:56
L15	1141	438/689	USPAT	OR	ON	2005/03/31 10:56
L16	3365	438/692	USPAT	OR	ON	2005/03/31 10:56
L17	1446	438/700	USPAT	OR	ON	2005/03/31 10:56
L18	381	438/663	USPAT	OR	ON	2005/03/31 10:57
L19	519	438/589	USPAT	OR	ON	2005/03/31 10:57
L20	641	438/593	USPAT	OR	ON	2005/03/31 10:57
L21	1848	438/706	USPAT	OR	ON	2005/03/31 10:57
L22	228	438/733	USPAT	OR	ON	2005/03/31 10:57
L23	964	438/738	USPAT	OR	ON	2005/03/31 10:57
L24	1466	438/745	USPAT	OR	ON	2005/03/31 10:57

S47 7	16	(stacked adj gate adj flash adj memory adj device)	USPAT	OR	ON	2005/03/31 09:37
S47 8	4	S477 and (trench and long and parallel and tunnel and oxide and isolation and source and drain and polysilicon and control and gate and plurality)	USPAT	OR	ON	2005/03/31 09:39
S47 9	4	S477 and (trench and long and parallel and tunnel and oxide and isolation and source and drain and polysilicon and control and gate and plurality and pair and floating and region)	USPAT	OR	ON	2005/03/31 09:46
S48 0	16	S477 and (trench or long or parallel or tunnel or oxide or isolation or source or drain or polysilicon or control or gate or plurality or pair or floating or region or electrically or bottom or memory or cell or side or wall or spacer or silicon or nitride or pad or shallow or dielectric or insulating or cvd or cmp or etch or etching or RTA)	USPAT	OR	ON	2005/03/31 10:54